



Features

MiniMELF case especially for automatic insertion. The Zener voltages are graded according to the international E24 standard. Smaller voltage tolerances and higher Zener voltages are upon request. These diodes are also available in DO-35 case with the type designation HBZX55C...



LL-34

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Power Dissipation ¹⁾	P_{tot}	500	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance Junction to Ambient ¹⁾	$R_{\theta\text{JA}}$	300	$^\circ\text{C/W}$

¹⁾ Valid provided that electrodes are kept at ambient temperature.



Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

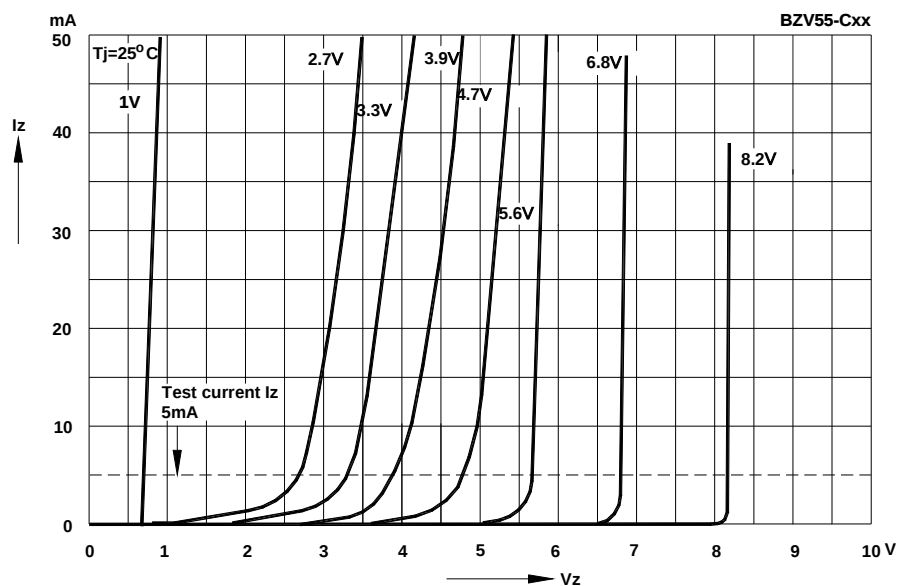
Type	Zener Voltage Range ¹⁾			Dynamic Resistance			Reverse Leakage Current			Temp. Coefficient of Zener Voltage
	V_{Znom}	V_{ZT}	at I_{ZT}	Z_{ZT}	Z_{ZK}	at I_{ZK}	$T_a = 25\text{ }^{\circ}\text{C}$	$T_a = 125\text{ }^{\circ}\text{C}$	at V_R	
	(V)	(V)	(mA)	Max. (Ω)	Max. (Ω)	(mA)	Max. (μA)	Max. (μA)	(V)	
HBZV55C1 ²⁾	0.75	0.7...0.8	5	8	50	1	-	-	-	-0.26...-0.23
HBZV55C2V0	2	1.8...2.15	5	85	600	1	100	200	1	-0.09...-0.06
HBZV55C2V2	2.2	2.08...2.33	5	85	600	1	75	160	1	-0.09...-0.06
HBZV55C2V4	2.4	2.28...2.56	5	85	600	1	50	100	1	-0.09...-0.06
HBZV55C2V7	2.7	2.5...2.9	5	85	600	1	10	50	1	-0.09...-0.06
HBZV55C3V0	3	2.8...3.2	5	85	600	1	4	40	1	-0.08...-0.05
HBZV55C3V3	3.3	3.1...3.5	5	85	600	1	2	40	1	-0.08...-0.05
HBZV55C3V6	3.6	3.4...3.8	5	85	600	1	2	40	1	-0.08...-0.05
HBZV55C3V9	3.9	3.7...4.1	5	85	600	1	2	40	1	-0.08...-0.05
HBZV55C4V3	4.3	4...4.6	5	75	600	1	1	20	1	-0.06...-0.03
HBZV55C4V7	4.7	4.4...5	5	60	600	1	0.5	10	1	-0.05...+0.02
HBZV55C5V1	5.1	4.8...5.4	5	35	550	1	0.1	2	1	-0.02...+0.02
HBZV55C5V6	5.6	5.2...6	5	25	450	1	0.1	2	1	-0.05...+0.05
HBZV55C6V2	6.2	5.8...6.6	5	10	200	1	0.1	2	2	0.03...0.06
HBZV55C6V8	6.8	6.4...7.2	5	8	150	1	0.1	2	3	0.03...0.07
HBZV55C7V5	7.5	7...7.9	5	7	50	1	0.1	2	5	0.03...0.07
HBZV55C8V2	8.2	7.7...8.7	5	7	50	1	0.1	2	6.2	0.03...0.08
HBZV55C9V1	9.1	8.5...9.6	5	10	50	1	0.1	2	6.8	0.03...0.09
HBZV55C10	10	9.4...10.6	5	15	70	1	0.1	2	7.5	0.03...0.1
HBZV55C11	11	10.4...11.6	5	20	70	1	0.1	2	8.2	0.03...0.11
HBZV55C12	12	11.4...12.7	5	20	90	1	0.1	2	9.1	0.03...0.11
HBZV55C13	13	12.4...14.1	5	26	110	1	0.1	2	10	0.03...0.11
HBZV55C15	15	13.8...15.6	5	30	110	1	0.1	2	11	0.03...0.11
HBZV55C16	16	15.3...17.1	5	40	170	1	0.1	2	12	0.03...0.11
HBZV55C18	18	16.8...19.1	5	50	170	1	0.1	2	13	0.03...0.11
HBZV55C20	20	18.8...21.2	5	55	220	1	0.1	2	15	0.03...0.11
HBZV55C22	22	20.8...23.3	5	55	220	1	0.1	2	16	0.04...0.12
HBZV55C24	24	22.8...25.6	5	80	220	1	0.1	2	18	0.04...0.12
HBZV55C27	27	25.1...28.9	5	80	220	1	0.1	2	20	0.04...0.12
HBZV55C30	30	28...32	5	80	220	1	0.1	2	22	0.04...0.12
HBZV55C33	33	31...35	5	80	220	1	0.1	2	24	0.04...0.12
HBZV55C36	36	34...38	5	80	220	1	0.1	2	27	0.04...0.12
HBZV55C39	39	37...41	2.5	90	500	0.5	0.1	5	30	0.04...0.12
HBZV55C43	43	40...46	2.5	90	500	0.5	0.1	5	33	0.04...0.12
HBZV55C47	47	44...50	2.5	110	600	0.5	0.1	5	36	0.04...0.12
HBZV55C51	51	48...54	2.5	125	700	0.5	0.1	10	39	0.04...0.12
HBZV55C56	56	52...60	2.5	135	700	0.5	0.1	10	43	0.04...0.12
HBZV55C62	62	58...66	2.5	150	1000	0.5	0.1	10	47	0.04...0.12
HBZV55C68	68	64...72	2.5	200	1000	0.5	0.1	10	51	0.04...0.12
HBZV55C75	75	70...79	2.5	250	1000	0.5	0.1	10	56	0.04...0.12

¹⁾ Tested with pulses $t_p = 20\text{ ms}$.

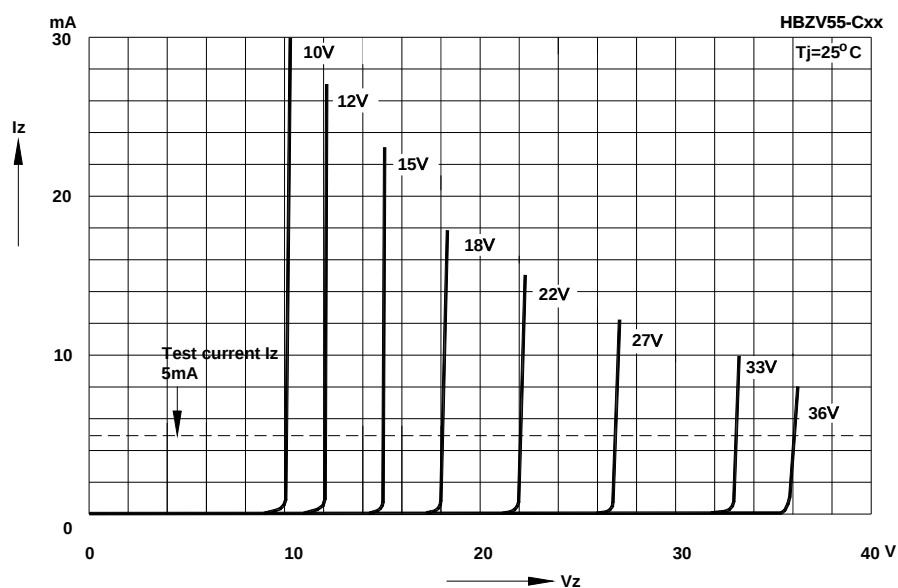
²⁾ The ZMM1 is a silicon diode with operation in forward direction. Hence, the index of all parameters should be "F" instead of "Z". Connect the cathode electrode to the negative pole.



Typical Characteristics

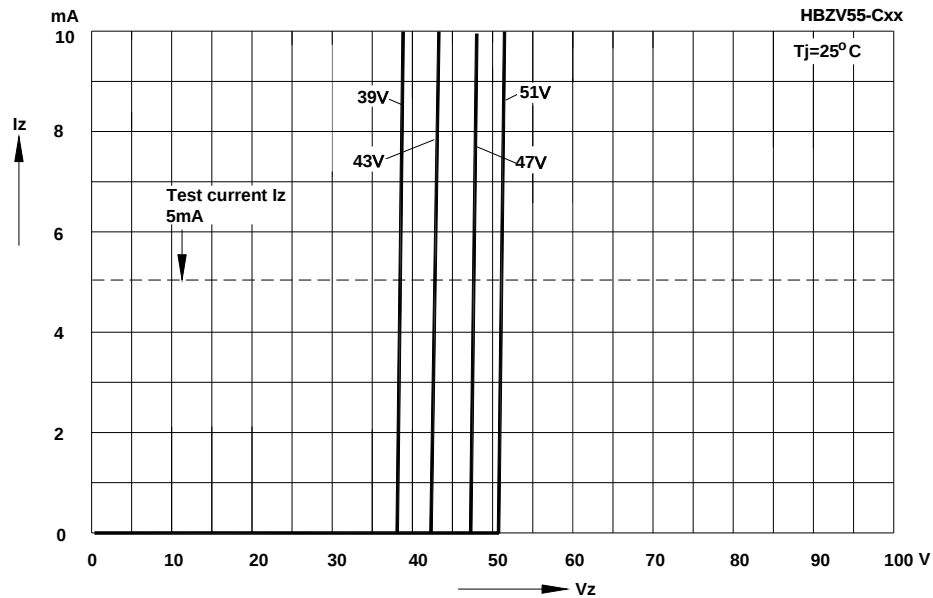


Breakdown characteristics
 $T_J = \text{constant (pulsed)}$

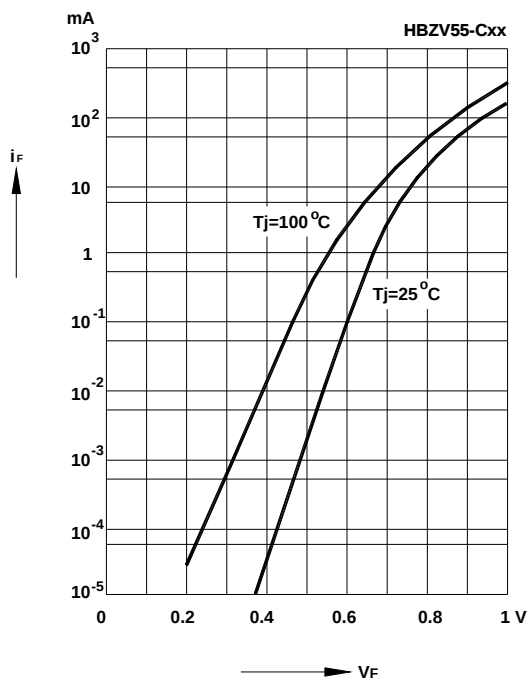




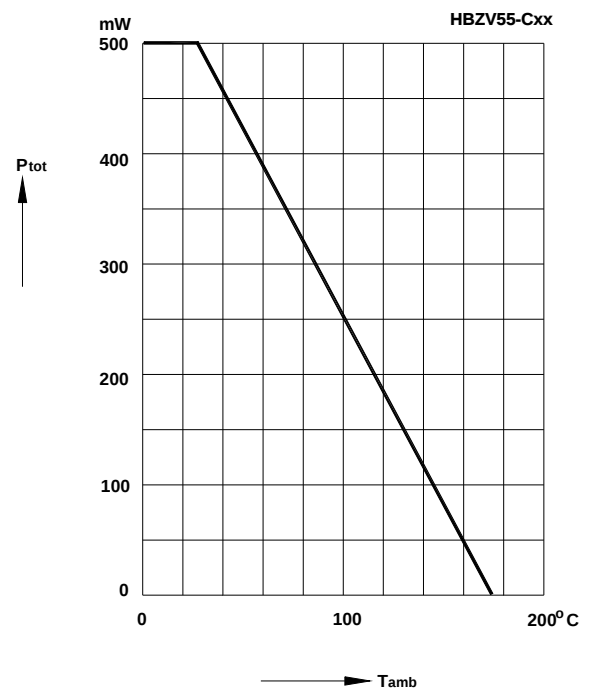
Breakdown characteristics
 $T_J = \text{constant (pulsed)}$



Forward characteristics

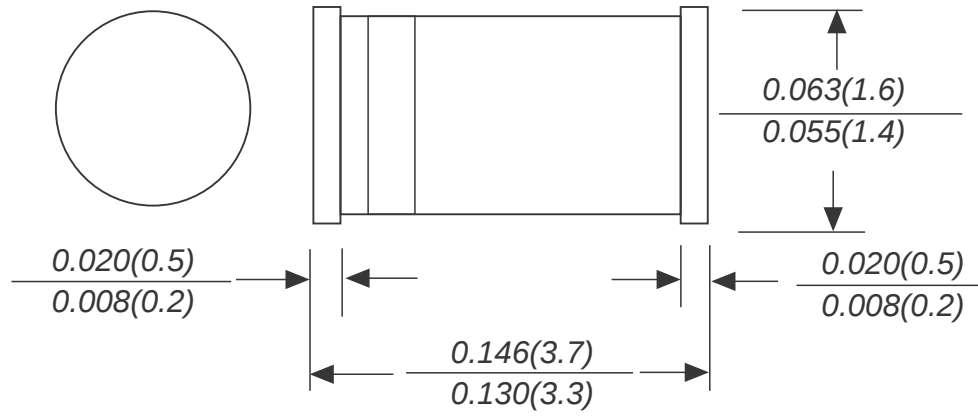


Admissible power dissipation
versus ambient temperature
Valid provided that electrodes are kept
at ambient temperature.





LL-34 Package Information



Dimensions in inches and (millimeters)



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